## **Tutorial Sheet - Lecture 14**

## **Optical Transitions**

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- 1) Describe, in your own words, using schematic diagrams as necessary;
  - a. Absorption
  - b. Spontaneous emission
  - c. Stimulated emission
- 2) Define the rates of the transitions above and describe how a change in carrier density can result in optical gain. Define the terms "inversion" and "transparency" in a real material used within a laser.
- 3) Derive the electronic density of states in three dimensions.
- 4) At room temperature, a direct band-gap semiconductor has a band-gap of 1.42 eV, and an absorption coefficient of 4x10<sup>6</sup> m<sup>-1</sup> at 750nm. Stating all assumptions;
  - a. Calculate the thickness of semiconductor required to absorb one half of the incident photons at 750nm.
  - b. Estimate the absorption coefficient at 650nm
  - c. Comment on the effect of increasing temperature on the absorption coefficient at 750nm.
  - d. Estimate the effect on the absorption coefficient of replacing the sample with a semiconductor with an effective mass half that of the original.